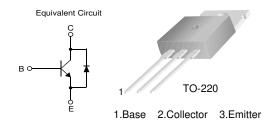


July 2008

FJP5304D NPN Silicon Transistor

High Voltage High Speed Power Switch Application

- · Wide Safe Operating Area
- Built-in Free Wheeling diodeSuitable for Electronic Ballast Application
- Suitable for Electronic Ballast Application
- · Small Variance in Storage Time



Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Value	
V _{CBO}	Collector-Base Voltage	700	V
V _{CEO}	Collector-Emitter Voltage	400	V
V _{EBO}	Emitter-Base Voltage	12	V
I _C	Collector Current (DC)	4	Α
I _{CP}	* Collector Current (Pulse)	8	Α
I _B	Base Current (DC)	2	Α
I _{BP}	* Base Current (Pulse)	4	Α
P _C	Collector Dissipation (T _C =25°C)	70	W
T _{STG}	Storage Temperature	- 65 ~ 150	°C

 $^{^{\}star}$ Pulse Test Pulse Width = 5ms, Duty Cycle $\geq 1.0\%$

Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	$I_{C} = 1 \text{mA}, I_{E} = 0$	700			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_{C} = 5mA, I_{B} = 0$	400			V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E = 1mA, I _C = 0	12			V
I _{CES}	Collector Cut-off Current	V _{CE} = 700V, V _{EB} = 0			100	mA
I _{CEO}	Collector Cut-off Current	V _{CE} = 400V, IB = 0			250	mA
I _{EBO}	Emitter Cut-off Current	V _{EB} = 12V, I _C = 0			100	mA

h _{FE}	DC Current Gain	$V_{CE} = 5V, I_{C} = 10mA$ $V_{CE} = 5V, I_{C} = 2A$	10 8		40	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_C = 0.5A, I_B = 0.1A$ $I_C = 1A, I_B = 0.2A$ $I_C = 2.5A, I_B = 0.5A$			0.7 1.0 1.5	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	$I_C = 0.5A, I_B = 0.1A$ $I_C = 1A, I_B = 0.2A$ $I_C = 2.5A, I_B = 0.5A$			1.1 1.2 1.3	V
V _f	Internal Diode Forward Voltage Drop	I _F = 2A			2.5	V
Inductive Lo	oad Switching (V _{CC} = 200V)					
t _{stg}	Storage Time	$I_C = 2A, I_{B1} = 0.4A$		0.6		μS
tf	Fall Time	$V_{BE}(off) = -5V, L = 200\mu H$		0.1		
Resistive Lo	oad Switching (V _{CC} = 250V)					
t _{stg}	Storage Time	$I_C = 2A$, $I_{B1} = I_{B2} = 0.4A$			2.9	μS
tf	Fall Time	T _P = 30μs		0.2		

^{*} Pulse test: PW \leq 300 μ s, Duty cycle \leq 2%

Thermal Characteristics

Symbol	Parameter	Max.	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.78	°C/W
$R_{ heta JA}$	Thermal Resistance, Junction to Ambient	62.5	°C/W

Typical Characteristics

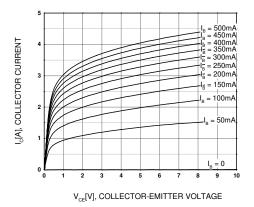


Figure 1. Static Characteristic

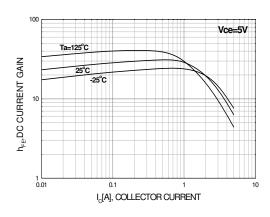


Figure 2. DC Current Gain

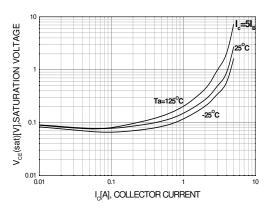


Figure 3. Collector-Emitter Saturation Voltage

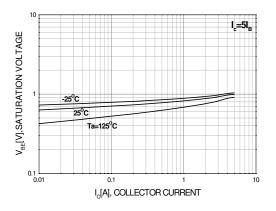


Figure 4. Base-Emitter Saturation Voltage

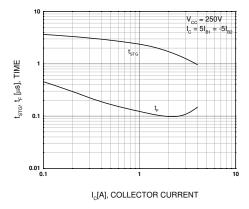


Figure 5. Resitive Load Switching Time

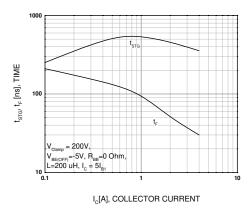


Figure 6. Inductive Load Switching Time

Typical Characteristics (Continued)

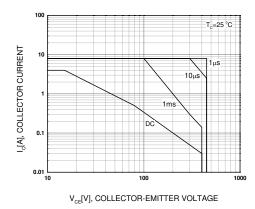


Figure 1. Forward Bias Safe Operating Area

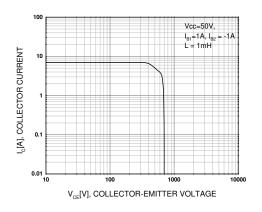


Figure 2. Reverse Bias Safe Operating Area

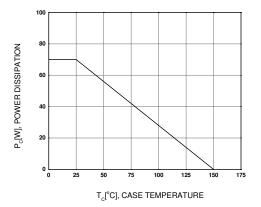
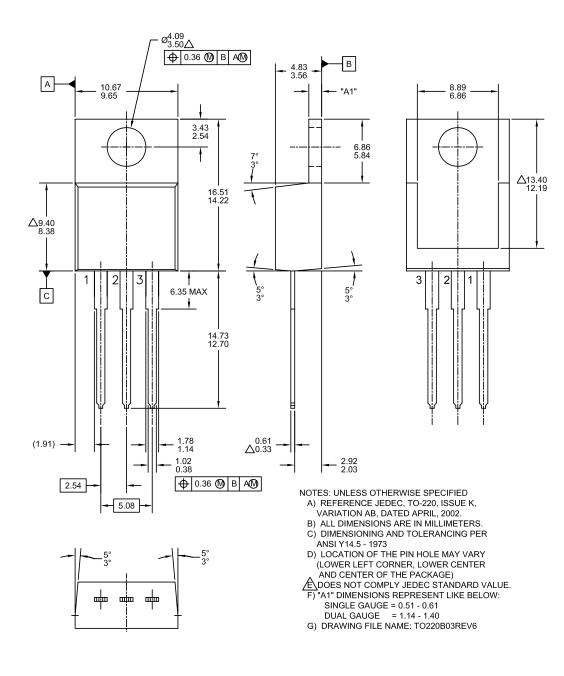


Figure 3. Power Derating

Mechanical Dimensions

TO220







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